Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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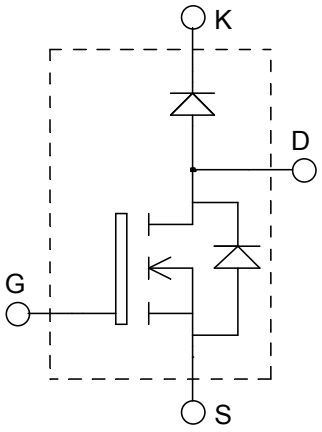
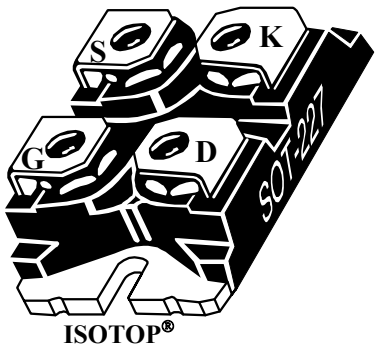
ISOTOP® Boost chopper Super Junction MOSFET Power Module

V_{DSS} = 600V
R_{DSon} = 70mΩ max @ Tj = 25°C
I_D = 40A @ Tc = 25°C





ISOTOP®

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- COOLMOS Power Semiconductors
  - Ultra low R_{DSon}
  - Low Miller capacitance
  - Ultra low gate charge
  - Avalanche energy rated
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	*Parameter*			*Max ratings*	*Unit*
V_{DSS}	Drain - Source Breakdown Voltage			600	V
I_D	Continuous Drain Current		T_c = 25°C	40	A
			T_c = 80°C	30	
I_{DM}	Pulsed Drain current			120	
V_{GS}	Gate - Source Voltage			±20	V
R_{DSon}	Drain - Source ON Resistance			70	mΩ
P_D	Maximum Power Dissipation		T_c = 25°C	290	W
I_{AR}	Avalanche current (repetitive and non repetitive)			20	A
E_{AR}	Repetitive Avalanche Energy			1	mJ
E_{AS}	Single Pulse Avalanche Energy			1800	
IF_{AV}	Maximum Average Forward Current	Duty cycle=0.5	Tc = 80°C	30	A
IF_{RMS}	RMS Forward Current (Square wave, 50% duty)			39	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ T_j = 25°C unless otherwise specified

Electrical Characteristics

Symbol	*Characteristic*	*Test Conditions*		*Min*	*Typ*	*Max*	*Unit*
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS} = 0V, V_{DS} = 600V	T_j = 25°C			25	µA
		V_{GS} = 0V, V_{DS} = 600V	T_j = 125°C			250	
$R_{DS(on)}$	Drain – Source on Resistance	V_{GS} = 10V, I_D = 20A				70	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 1mA		2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0V				±100	nA

Dynamic Characteristics

Symbol	*Characteristic*	*Test Conditions*	*Min*	*Typ*	*Max*	*Unit*
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1MHz		7015		pF
C_{oss}	Output Capacitance			2565		
C_{rss}	Reverse Transfer Capacitance			212		
Q_g	Total gate Charge	V_{GS} = 10V V_{Bus} = 300V I_D = 40A		259		nC
Q_{gs}	Gate – Source Charge			29		
Q_{gd}	Gate – Drain Charge			111		
$T_{d(on)}$	Turn-on Delay Time	**Resistive Switching** V_{GS} = 15V V_{Bus} = 380V I_D = 40A R_G = 1.8Ω		20		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			115		
T_f	Fall Time			10		
Eon	Turn-on Switching Energy	**Inductive switching @ 25°C** V_{GS} = 15V, V_{Bus} = 400V I_D = 40A, R_G = 5Ω		670		µJ
Eoff	Turn-off Switching Energy			980		
Eon	Turn-on Switching Energy	**Inductive switching @ 125°C** V_{GS} = 15V, V_{Bus} = 400V I_D = 40A, R_G = 5Ω		1100		µJ
Eoff	Turn-off Switching Energy			1206		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_F	Diode Forward Voltage	I_F = 30A			1.6	1.8	V
		I_F = 60A			1.9		
		I_F = 30A	T_j = 125°C		1.4		
I_{RM}	Maximum Reverse Leakage Current	V_R = 600V	T_j = 25°C			250	µA
		V_R = 600V	T_j = 125°C			500	
C_T	Junction Capacitance	V_R = 200V			44		pF
t_{rr}	Reverse Recovery Time	I_F=1A,V_R=30V di/dt =100A/µs	T_j = 25°C		23		ns
	Reverse Recovery Time	I_F = 30A V_R = 400V di/dt =200A/µs	T_j = 25°C		85		
			T_j = 125°C		160		
I_{RRM}	Maximum Reverse Recovery Current		T_j = 25°C		4		A
			T_j = 125°C		8		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		130		nC
			T_j = 125°C		700		
t_{rr}	Reverse Recovery Time	I_F = 30A V_R = 400V di/dt =1000A/µs	T_j = 125°C		70		ns
Q_{rr}	Reverse Recovery Charge				1300		nC
I_{RRM}	Maximum Reverse Recovery Current				30		A

Thermal and package characteristics

Symbol	Characteristic		Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	CoolMos			0.43	°C/W
		Diode			1.21	
R_{thJA}	Junction to Ambient (IGBT & Diode)				20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz		2500			V
T_J,T_{STG}	Storage Temperature Range		-55		150	°C
T_L	Max Lead Temp for Soldering:0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

Typical CoolMOS Performance Curve

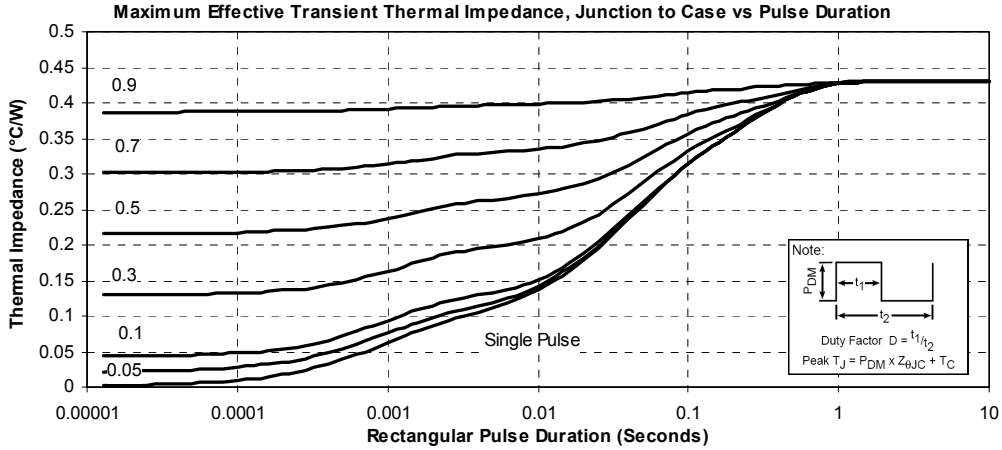


Fig 1, Maximum Effective transient thermal Impedance, Junction to case vs Pulse Duration

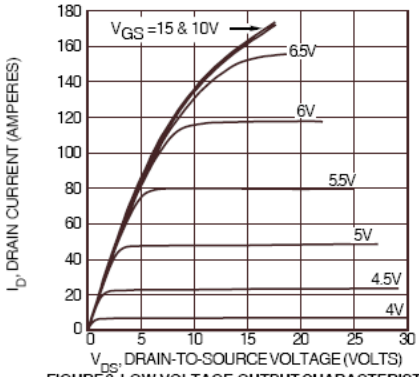


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

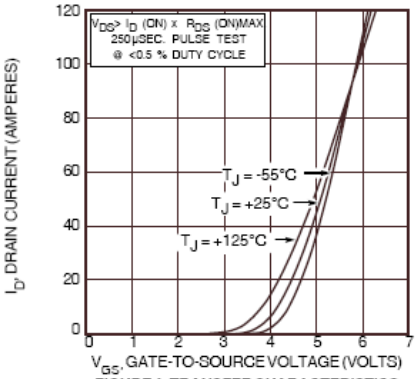


FIGURE 4, TRANSFER CHARACTERISTICS

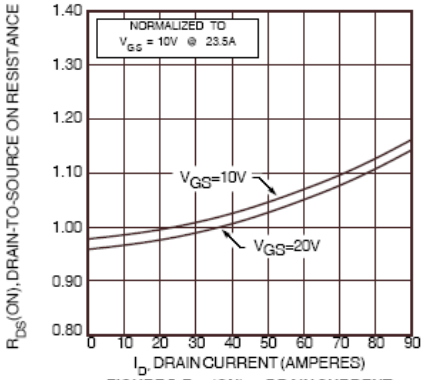


FIGURE 5, R_{DS}(ON) vs DRAIN CURRENT

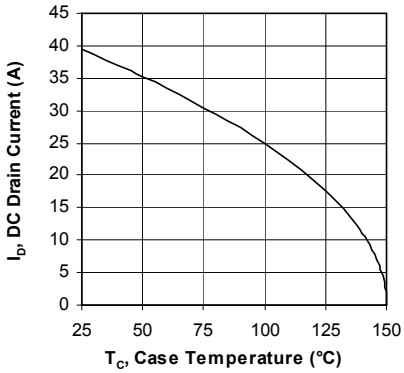


Figure 6, DC Drain Current vs Case Temperature

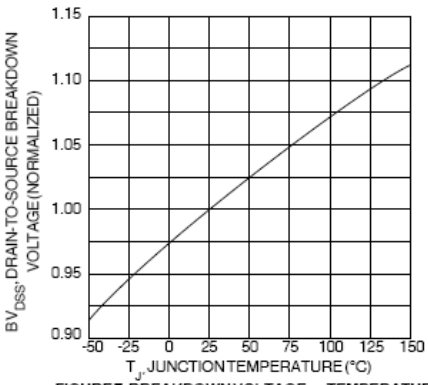


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

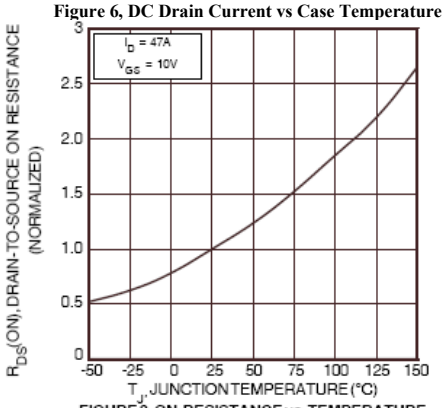


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

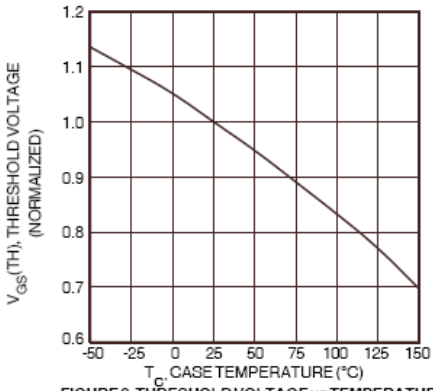


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

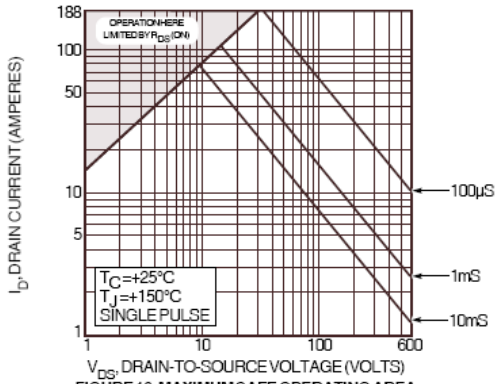


FIGURE 10, MAXIMUM SAFE OPERATING AREA

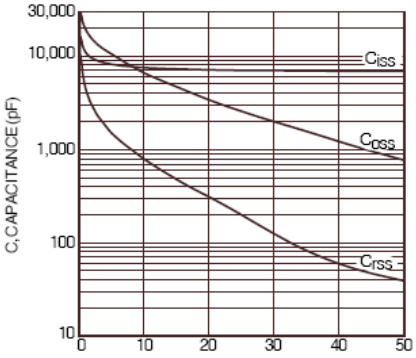


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

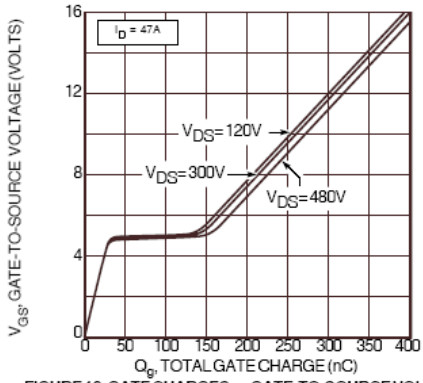


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

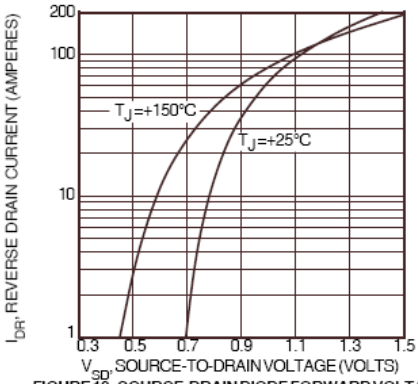


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

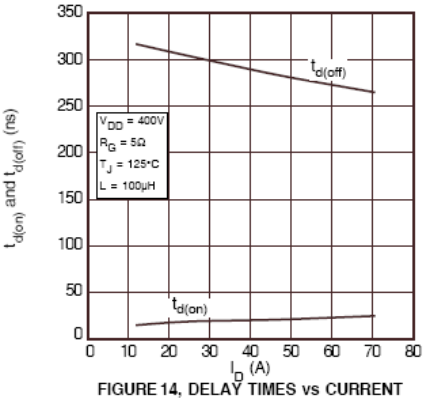


FIGURE 14, DELAY TIMES vs CURRENT

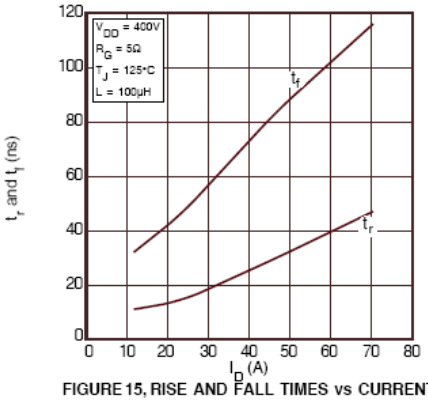


FIGURE 15, RISE AND FALL TIMES vs CURRENT

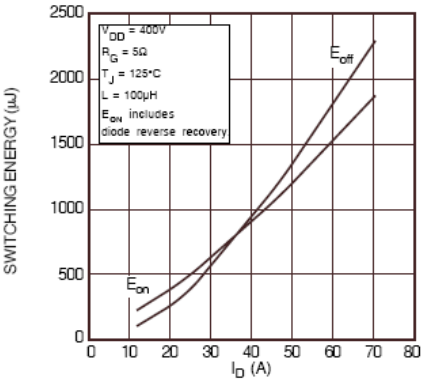


FIGURE 16, SWITCHING ENERGY vs CURRENT

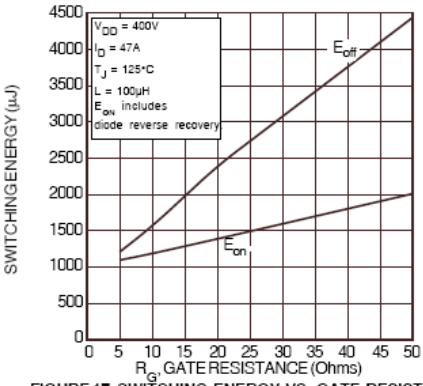


FIGURE 17, SWITCHING ENERGY VS. GATE RESISTANCE

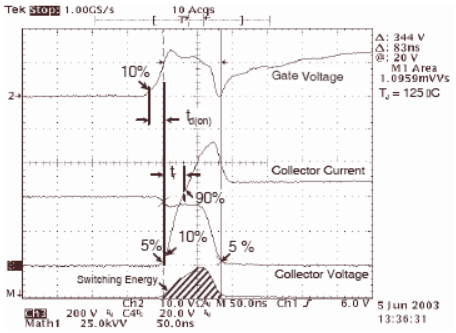


Figure 18, Turn-on Switching Waveforms and Definitions

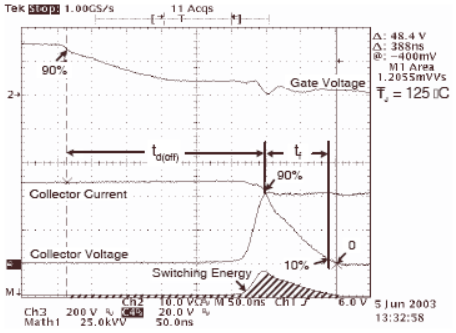


Figure 19, Turn-off Switching Waveforms and Definitions

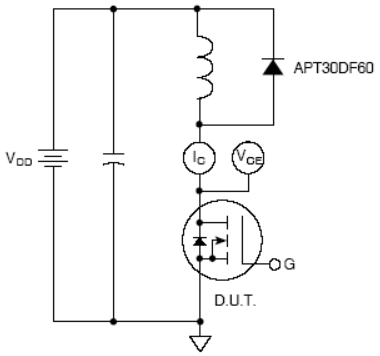


Figure 20, Inductive Switching Test Circuit

Typical Diode Performance Curve

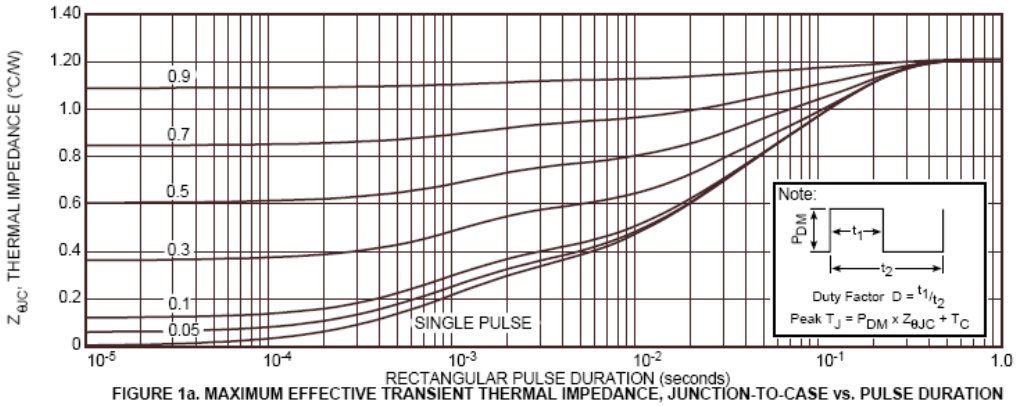


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

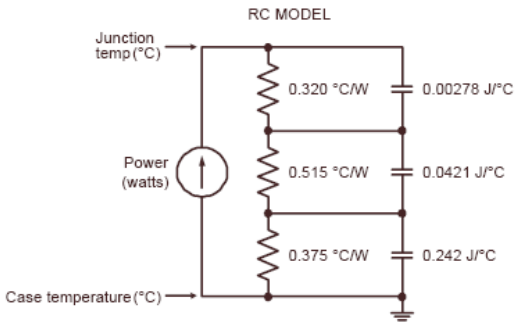


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

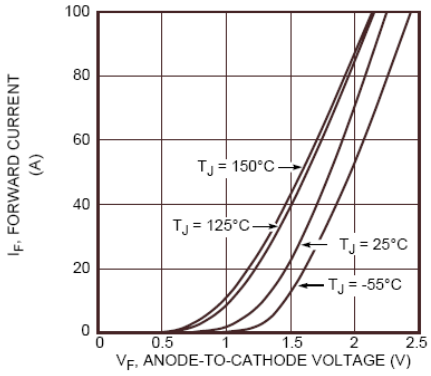


Figure 2. Forward Current *vs.* Forward Voltage

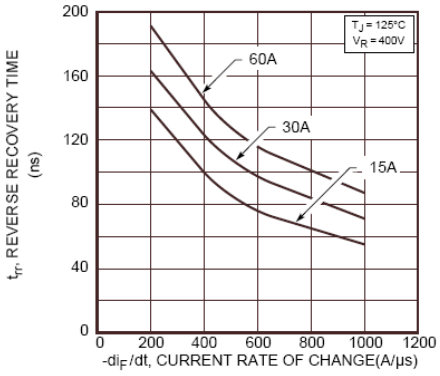


Figure 3. Reverse Recovery Time *vs.* Current Rate of Change

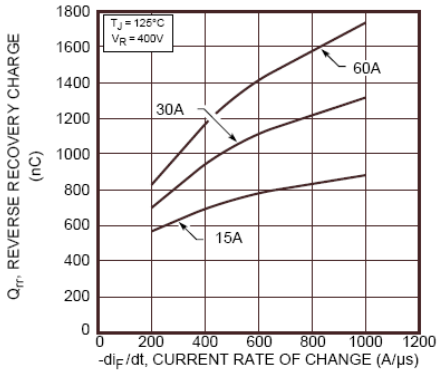


Figure 4. Reverse Recovery Charge *vs.* Current Rate of Change

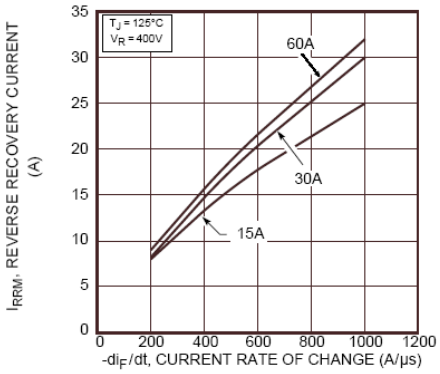


Figure 5. Reverse Recovery Current *vs.* Current Rate of Change

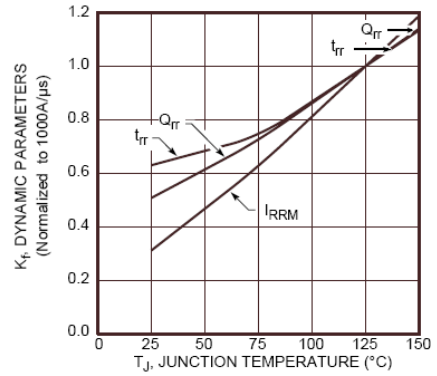


Figure 6. Dynamic Parameters *vs.* Junction Temperature

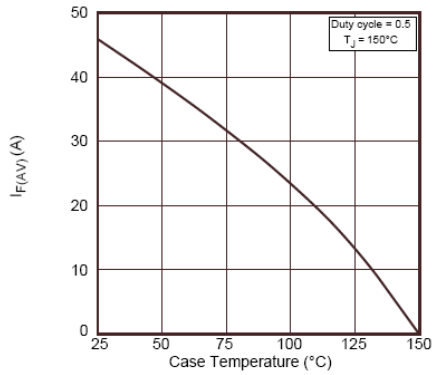


Figure 7. Maximum Average Forward Current *vs.* CaseTemperature

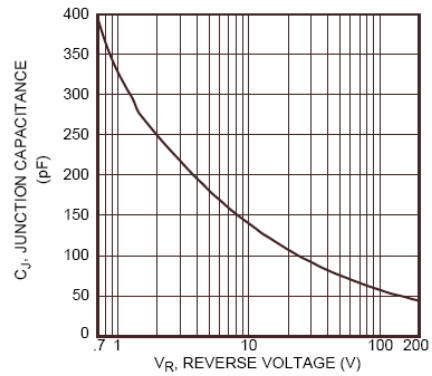


Figure 8. Junction Capacitance *vs.* Reverse Voltage

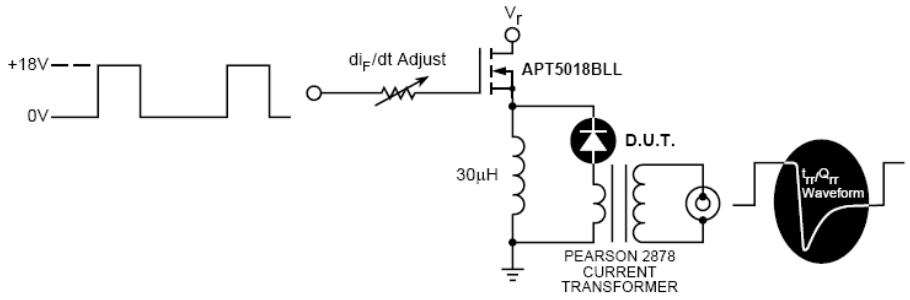


Figure 9. Diode Test Circuit

1. I_F - Forward Conduction Current
2. di_F/dt - Rate of Diode Current Change Through Zero Crossing.
3. I_{RRM} - Maximum Reverse Recovery Current.
4. t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \bullet I_{RRM}$ passes through zero.
5. Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr}.

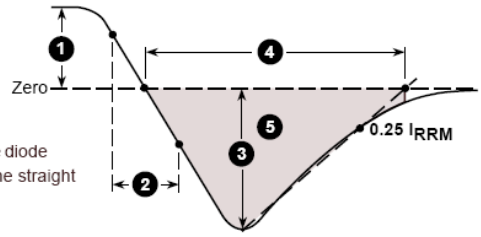
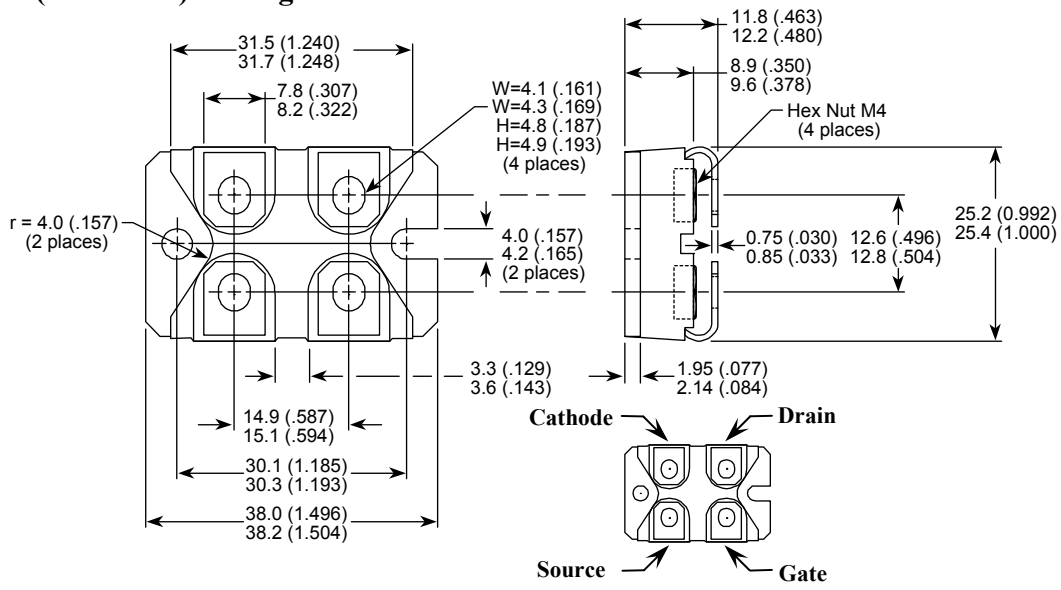


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

"COOLMOS™ comprise a new family of transistors developed by Infineon Technologies AG. "COOLMOS" is a trademark of Infineon Technologies AG".

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Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.